Publications – Communications relatives au projet P-14-00765

Etude de la croissance localisée de semi-conducteurs III-V

Publications

1. DESPLANQUE L., FAHED M., HAN X., CHINNI V.K., TROADEC D., CHAUVAT M.P., RUTERANA P., and WALLART X.,
Influence of nanoscale faceting on the tunneling properties of near broken gap InAs/AlGaSb heterojunctions grown by selective area epitaxy, Nanotechnology **25**, 465302 (2014)

2. FAHED M., DESPLANQUE L., COINON C., TROADEC D., WALLART X.,
Impact of P/In flux ratio and epilayer thickness on faceting for nanoscale selective area growth of InP by molecular beam epitaxy, Nanotechnology **26** , 295301 (2015)

3. FAHED M., DESPLANQUE L., TROADEC D., PATRIARCHE G., WALLART X.,
Selective area heteroepitaxy of GaSb on GaAs (001) for in-plane InAs nanowire achievement, Nanotechnology **27**, 505301 (2016)

4. FAHED M., DESPLANQUE L., TROADEC D., PATRIARCHE G., WALLART X.,
Threading dislocation free GaSb nanotemplates grown by selective molecular beam epitaxy on GaAs (001) for in-plane InAs nanowire integration, J. Cryst. Growth, available online december 9, 2016 ; in press (2017)

Communications

1. FAHED M., DESPLANQUE L., COINON C., CODRON J.L., TROADEC D., WALLART X.,
Nanoscale selective area growth of InP by molecular beam epitaxy : influence of the P/In flux ratio on the faceting, European Materials Research Society Spring Meeting, E-MRS Spring 2015, Symposium I - Semiconductor nanostructures towards electronic and opto-electronic device applications - V, Lille, France, may 11-15, 2015 (orale)

2. DESPLANQUE L., HAN X.L., FAHED M., CHINNI V.K., TROADEC D., CHAUVAT M.P., RUTERANA P., WALLART X.,
InAs/AlGaSb Esaki tunnel diodes grown by selective area epitaxy on GaSb (001) substrate, Proceedings of 26th International Conference on Indium Phosphide and Related Materials, IPRM 2014, Compound Semiconductor Week, CSW 2014, Montpellier, France, may 11-15, 2014, paper Mo-C1-6 (orale)

3. DESPLANQUE L., HAN X., FAHED M., CHINNI V.K., TROADEC D., CHAUVAT M.P., RUTERANA P., and WALLART X.,
Selective Area Epitaxy of InAs/AlGaSb Heterostructures on GaSb (001) Substrate for Tunnel Diode Applications, 18th International Conference on Molecular Beam Epitaxy, September 7-12, 2014, Flagstaff, Arizona (poster)

4. DESPLANQUE L., FAHED M., TROADEC D., RUTERANA P., WALLART X.,
Selective area growth of GaSb nano-templates on GaAs (001) using atomic hydrogen assisted molecular beam epitaxy, 28th International Conference on Indium Phosphide and Related Materials, IPRM 2016, Toyama, Japan, paper MoP-IPRM-002, june 26-30, 2016 (poster)

5. FAHED M., DESPLANQUE L., TROADEC D., WANG Y., RUTERANA P., PATRIARCHE G., WALLART X.,

Selective area growth of in-plane InAs nanowires on GaAs (001) using atomic hydrogen-assisted molecular beam epitaxy, 19th International Conference on Molecular Beam Epitaxy, MBE 2016, Montpellier, France, september 4-9, 2016 (orale)

6. DESPLANQUE L., PASTOREK M., FADJIE A.B., WICHMANN N., BOLLAERT S., WALLART X.,

Selective area MBE growth of InGaAs on InP for MOSFET applications, 19th International Conference on Molecular Beam Epitaxy, MBE 2016, Montpellier, France, september 4-9, 2016 (orale)